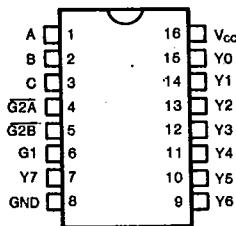


**KS54AHCT 138  
KS74AHCT****3-Line to 8-Line Decoders/Demultiplexers****FEATURES**

- Designed specifically for high-speed memory decoders and data transmission systems
- Incorporates 3 enable inputs to simplify cascading and/or data reception
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:  
 $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5V$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:  
KS74AHCT:  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$   
KS54AHCT:  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

**PIN CONFIGURATION****FUNCTION TABLE**

Enable Inputs	Select Inputs	Outputs							
		Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	H	X X X	H	H	H	H	H	H	H
L	X	X X X	H	H	H	H	H	H	H
H	L	L L L	L	H	H	H	H	H	H
H	L	L L H	H	L	H	H	H	H	H
H	L	L H L	H	H	L	H	H	H	H
H	L	L H H	H	H	H	L	H	H	H
H	L	H L L	H	H	H	H	L	H	H
H	L	H L H	H	H	H	H	H	L	H
H	L	H H L	H	H	H	H	H	H	L
H	L	H H H	H	H	H	H	H	H	L

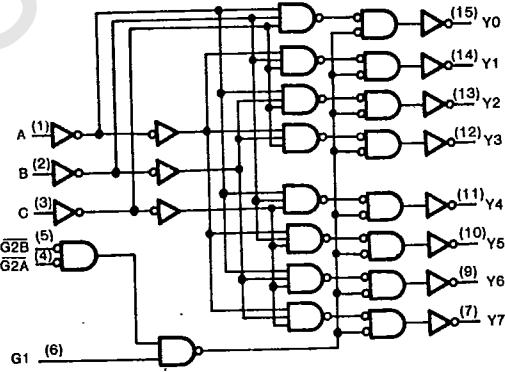
•  $G_2 = G_2A + G_2B$ **DESCRIPTION**

These devices are designed to be used in high-performance memory-decoding or data-routing applications requiring very short propagation delay times. In high-performance memory systems, these decoders can be used to minimize the effects of system decoding. When used with high-speed memories utilizing a fast-enable circuit, the delay times of these decoders and the enable time of the memory are usually less than the typical access time of the memory. This means that the effective system delay introduced by the decoder is negligible.

The conditions at the binary select inputs and the three enable inputs select one of eight input lines. Two active-low and one active-high enable inputs reduce the need for external gates or inverters when expanding. A 24-line decoder can be implemented without external inverters and a 32-line decoder requires only one inverter. An enable input can be used as a data input for demultiplexing applications.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

**LOGIC DIAGRAM**

SAMSUNG SEMICONDUCTOR

KS54AHCT 138  
KS74AHCT

3-Line to 8-Line Decoders/Demultiplexers

**Absolute Maximum Ratings\***

Supply Voltage Range, V <sub>CC</sub> , . . . . .	-0.5V to +7V
DC Input Diode Current, I <sub>IK</sub>	
(V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> +0.5V) . . . . .	±20 mA
DC Output Diode Current, I <sub>OK</sub>	
(V <sub>O</sub> < -0.5V or V <sub>O</sub> > V <sub>CC</sub> +0.5V) . . . . .	±20 mA
Continuous Output Current Per Pin, I <sub>O</sub>	
(-0.5V < V <sub>O</sub> < V <sub>CC</sub> +0.5V) . . . . .	±35 mA
Continuous Current Through	
V <sub>CC</sub> or GND pins . . . . .	±125 mA
Storage Temperature Range, T <sub>STG</sub> . . . . .	-65°C to +150°C
Power Dissipation Per Package, P <sub>D</sub> †	500 mW

\* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:

Plastic Package (N): -12mW/°C from 65°C to 85°C  
Ceramic Package (J): -12mW/°C from 100°C to 125°C**Recommended Operating Conditions**

Supply Voltage, V <sub>CC</sub>	4.5V to 5.5V
DC Input & Output Voltages*, V <sub>IN</sub> , V <sub>OUT</sub>	0V to V <sub>CC</sub>
Operating Temperature	

Range	KS74AHCT: -40°C to +85°C
	KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t<sub>r</sub>, t<sub>f</sub> . . . . . Max 500 ns\* Unused inputs must always be tied to an appropriate logic voltage level (either V<sub>CC</sub> or GND)**DC ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub>=5V±10% Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	T <sub>A</sub> =25°C	KS74AHCT		KS54AHCT T <sub>A</sub> = -40°C to +85°C T <sub>A</sub> = -55°C to +125°C	Unit
			Typ	Guaranteed Limits			
Minimum High-Level Input Voltage	V <sub>IH</sub>			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V <sub>IL</sub>			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =-20µA I <sub>O</sub> =-4mA	V <sub>CC</sub> 4.2	V <sub>CC</sub> -0.1 3.98	V <sub>CC</sub> -0.1 3.84	V <sub>CC</sub> -0.1 3.7	V
Maximum Low-Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =20µA I <sub>O</sub> =4mA I <sub>O</sub> =8mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I <sub>IN</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND		±0.1	±1.0	±1.0	µA
Maximum Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0µA		8.0	80.0	160.0	µA
Additional Worst Case Supply Current	ΔI <sub>CC</sub>	per input pin V <sub>I</sub> =2.4V other Inputs: at V <sub>CC</sub> or GND I <sub>OUT</sub> =0µA		2.7	2.9	3.0	mA



SAMSUNG SEMICONDUCTOR

**KS54AHCT 138****3-Line to 8-Line Decoders/Demultiplexers**

T-67-21-55

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r$ ,  $t_f \leq 2$  ns), AHCT138

Characteristic	Symbol	Conditions <sup>†</sup>	<b>KS74AHCT</b>	<b>KS54AHCT</b>		Unit
			$T_a = 25^\circ C$ $V_{cc} = 5.0V$	$T_a = -40^\circ C$ to $+85^\circ C$ $V_{cc} = 5.0V \pm 10\%$	$T_a = -55^\circ C$ to $+125^\circ C$ $V_{cc} = 5.0V \pm 10\%$	
		Typ	Min	Max	Min	Max
Propagation Delay, A, B, C or any Y	$t_{PLH}$		12	20	24	ns
	$t_{PHL}$		12	20	24	
Propagation Delay, G1 to any Y	$t_{PLH}$	$C_L = 50pF$	10	17	20	ns
	$t_{PHL}$		10	17	20	
Propagation Delay, G2A or G2B to any Y	$t_{PLH}$		10	17	20	ns
	$t_{PHL}$		10	17	20	
Input Capacitance	$C_{IN}$		5			pF
Power Dissipation Capacitance*	$C_{PD}$		50			pF

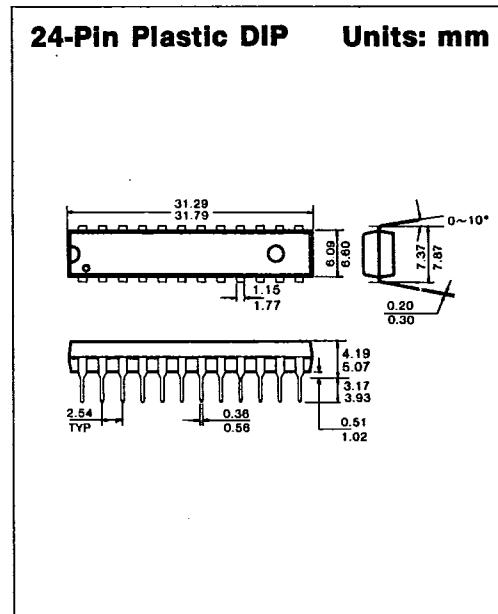
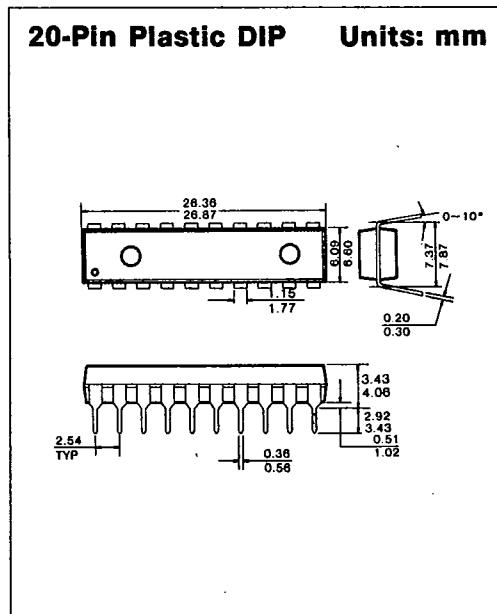
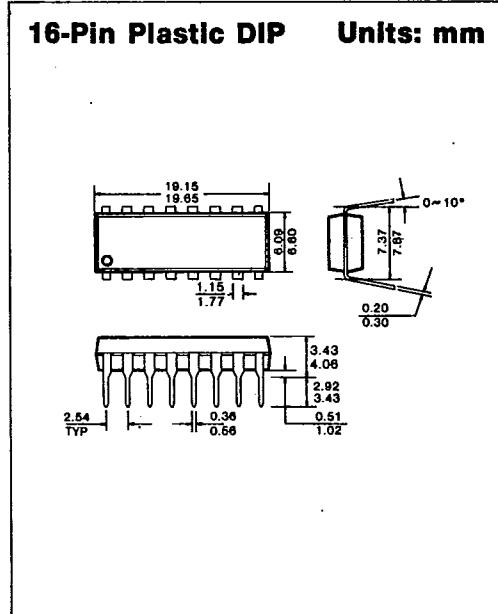
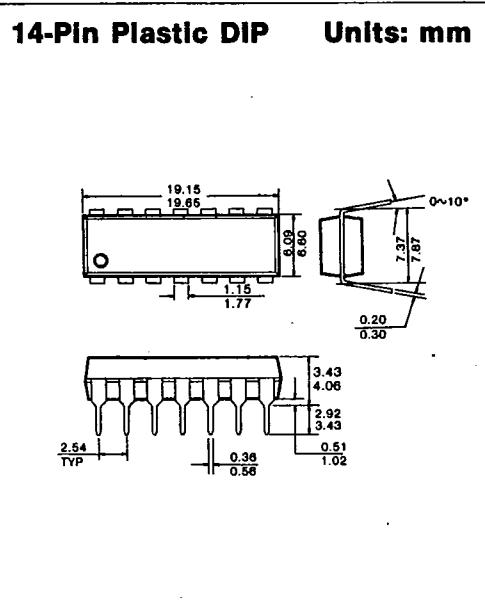
\*  $C_{PD}$  determines the no-load dynamic power dissipation:  $P_D = C_{PD} V_{cc}^2 f + I_{cc} V_{cc}$ .

† For AC switching test circuits and timing waveforms see section 2.

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SAMSUNG SEMICONDUCTOR

**PACKAGE DIMENSIONS**T-90-20**1. PLASTIC PACKAGES**

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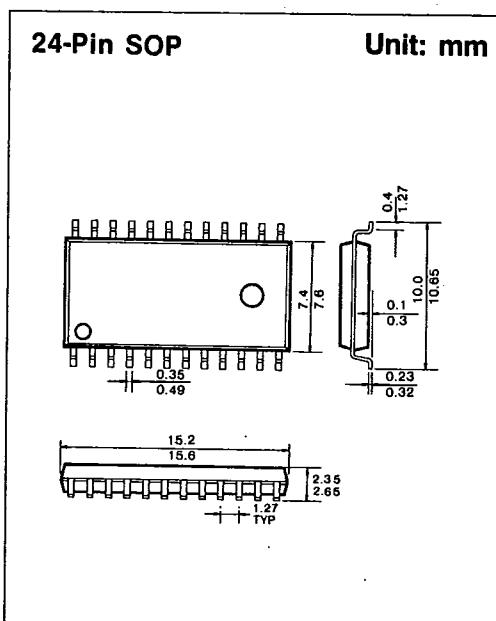
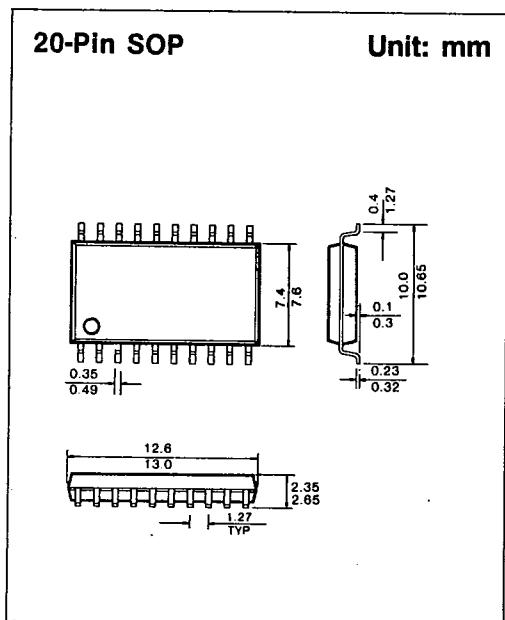
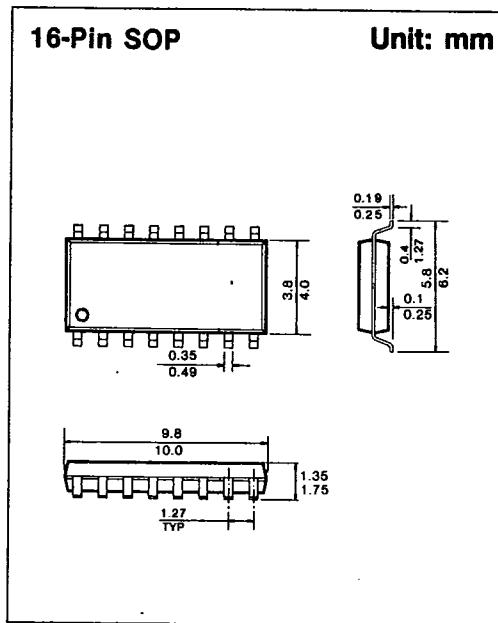
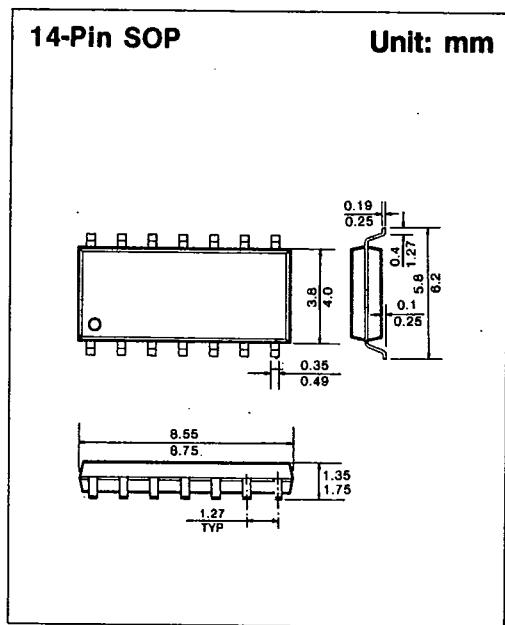


SAMSUNG SEMICONDUCTOR

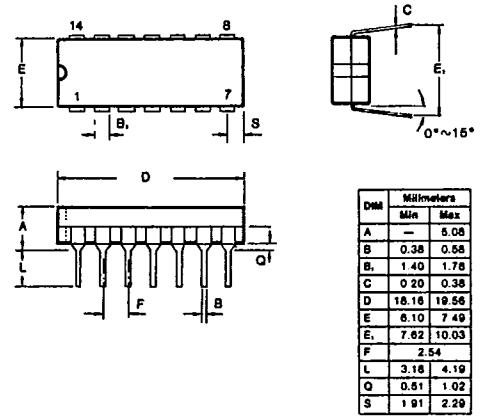
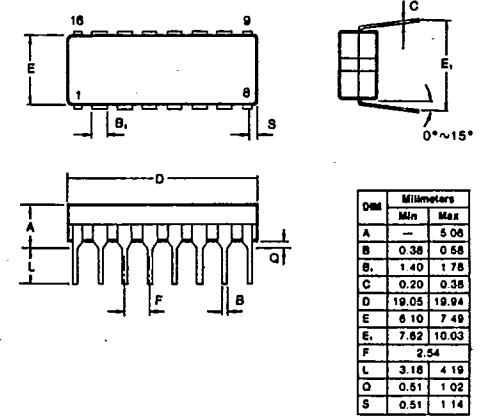
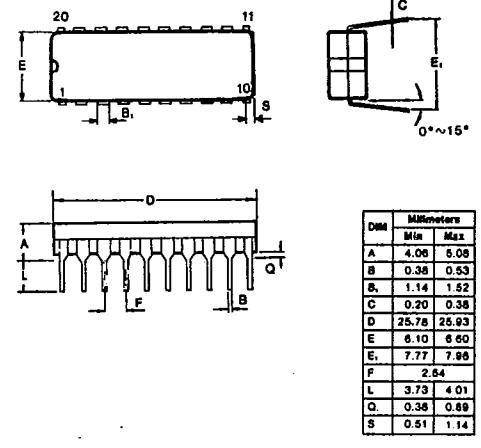
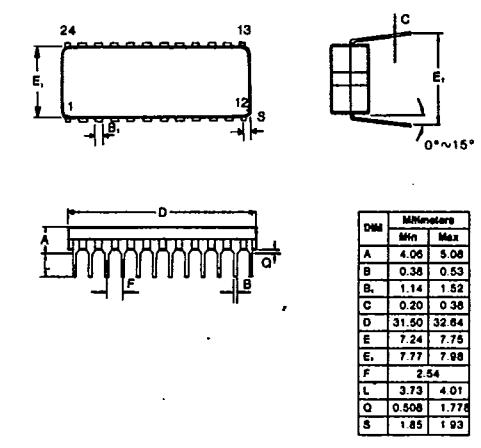
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**PACKAGE DIMENSIONS****T-90-20****SAMSUNG SEMICONDUCTOR****1676****A-05**

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**PACKAGE DIMENSIONS**T-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

7



SAMSUNG SEMICONDUCTOR

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